

# NB3U1548C

## 3.3V/2.5V/1.8V/1.5V 160 MHz 1:4 LVC MOS/LVTTL Low Skew Over Voltage Tolerant Fanout Buffer

### Description

The NB3U1548C is an LVC MOS, overvoltage tolerant clock fanout buffer targeted for clock generation in high performance telecommunication, networking and computing applications. The device is optimized for low skew clock distribution in low voltage applications. The input overvoltage tolerance enables using this device in mixed mode voltage applications. An output enable pin controls whether the outputs are in the active or high impedance state. Guaranteed output skew characteristics make the NB3U1548C ideal for those applications demanding well defined performance and repeatability. The NB3U1548C is packaged in a small SOIC-8 and in a TSSOP-8 package.

### Features

- Low skew 1:4 Fanout Buffer
- Supports 3.3 V, 2.5 V, 1.8 V and 1.5 V Power Supplies
- LVC MOS Input and Output Levels
- 3.6 V Overvoltage Tolerance at the Clock and Control Inputs
- Supports Clock Frequencies up to 160 MHz
- LVC MOS Compatible Control Input for Output Disable
- Output Disabled to a High Impedance State
- -40°C to 85°C Ambient Operating Temperature
- Available in Pb-Free RoHS Compliant Packages (SOIC-8, TSSOP-8)
- These Devices are Pb-Free and are RoHS Compliant

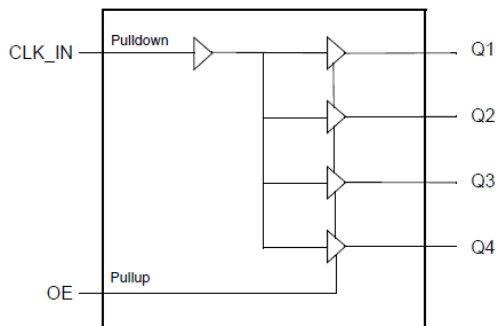


Figure 1. Block Diagram



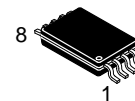
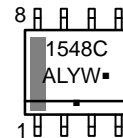
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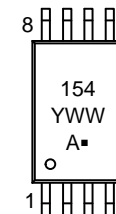
### MARKING DIAGRAMS



SOIC-8  
D SUFFIX  
CASE 751



TSSOP-8  
DT SUFFIX  
CASE 948S



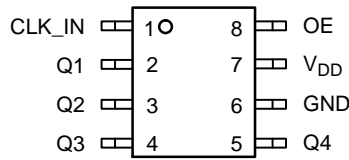
A = Assembly Location  
L = Wafer Lot  
Y = Year  
W, WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information on page 9 of this data sheet.

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**Figure 2. Pin Configuration (Top View)**

**Table 1. PIN DESCRIPTIONS**

Number	Name	Type		Description
1	CLK_IN	Input	Pulldown	Single-ended clock input. LVCMOS interface levels.
2	Q1	Output		Single-ended clock output. LVCMOS interface levels.
3	Q2	Output		Single-ended clock output. LVCMOS interface levels.
4	Q3	Output		Single-ended clock output. LVCMOS interface levels.
5	Q4	Output		Single-ended clock output. LVCMOS interface levels.
6	GND	Power		Power supply ground.
7	VDD	Power		Power supply pin.
8	OE	Input	Pullup	Output enable pin. See Table 3. LVCMOS interface levels.

NOTE: Pullup and Pulldown refer to internal input resistors. See Table 2, Pin Characteristics, for typical values.

**Table 2. PIN CHARACTERISTICS**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
CIN	Input Capacitance			4		pF
CPD	Power Dissipation Capacitance	V <sub>DD</sub> = 3.465 V		14		pF
		V <sub>DD</sub> = 2.375 V		13		pF
		V <sub>DD</sub> = 1.95 V		13		pF
		V <sub>DD</sub> = 1.6 V		12		pF
RPULLUP	Input Pullup Resistor			51		kΩ
RPULLDOWN	Input Pulldown Resistor			51		kΩ
ROUT	Output Impedance	V <sub>DD</sub> = 3.3 V ± 5%		9		Ω
		V <sub>DD</sub> = 2.5 V ± 5%		10		Ω
		V <sub>DD</sub> = 1.8 V ± 0.15 V		12		Ω
		V <sub>DD</sub> = 1.5 ± 0.1 V		15		Ω

## Function Table

**Table 3. OE CONFIGURATION TABLE**

Input	Operation
OE	
0	Q[4:1] disabled (high-impedance)
1 (default)	Q[4:1] enabled

NOTE: OE is an asynchronous control.

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**Table 4. ABSOLUTE MAXIMUM RATINGS**

Item	Rating
Supply Voltage, $V_{DD}$	4.6 V
Inputs, $V_I$	3.6 V
Outputs, $V_O$	-0.5 V to $V_{DD} + 0.5$ V
Package Thermal Impedance, $\theta_{JA}$ 8 Lead SOIC 8 Lead TSSOP	102.5°C/W (0 mps) 151.2°C/W (0 mps)
Storage Temperature, $T_{STG}$	-65°C to 150°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. JEDEC standard multilayer board – 2S2P (2 signal, 2 power) with 6 cm<sup>2</sup> copper area.
2. For additional information, see Application Note AND8003/D.

**Table 5. DC ELECTRICAL CHARACTERISTICS**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**POWER SUPPLY DC CHARACTERISTICS,  $V_{DD} = 3.3$  V  $\pm$  5%,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

$V_{DD}$	Power Supply Voltage		3.135	3.3	3.465	V
$I_{DDQ}$	Quiescent Power Supply Current	Inputs Open, Outputs Unloaded			1	mA

**POWER SUPPLY DC CHARACTERISTICS,  $V_{DD} = 2.5$  V  $\pm$  5%,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

$V_{DD}$	Power Supply Voltage		2.375	2.5	2.625	V
$I_{DDQ}$	Quiescent Power Supply Current	Inputs Open, Outputs Unloaded			1	mA

**POWER SUPPLY DC CHARACTERISTICS,  $V_{DD} = 1.8$  V  $\pm$  0.15 V,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

$V_{DD}$	Power Supply Voltage		1.65	1.8	1.95	V
$I_{DDQ}$	Quiescent Power Supply Current	Inputs Open, Outputs Unloaded			1	mA

**POWER SUPPLY DC CHARACTERISTICS,  $V_{DD} = 1.5$  V  $\pm$  0.1 V,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

$V_{DD}$	Power Supply Voltage		1.4	1.5	1.6	V
$I_{DDQ}$	Quiescent Power Supply Current	Inputs Open, Outputs Unloaded			1	mA

**LVC MOS DC CHARACTERISTICS,  $V_{DD} = 3.3$  V  $\pm$  5%,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

$V_{IH}$	Input High Voltage		$0.65 * V_{DD}$		3.6	V
$V_{IL}$	Input Low Voltage		-0.3		$0.35 * V_{DD}$	V
$I_{IH}$	Input High Current	CLK_IN	$V_{DD} = V_{IN} = 3.465$ V		165	$\mu\text{A}$
		OE	$V_{DD} = V_{IN} = 3.465$ V		5	$\mu\text{A}$
$I_{IL}$	Input Low Current	CLK_IN	$V_{DD} = 3.465$ V, $V_{IN} = 0$ V	-5		$\mu\text{A}$
		OE	$V_{DD} = 3.465$ V, $V_{IN} = 0$ V	-150		$\mu\text{A}$
$V_{OH}$	Output High Voltage	Q[4:1]	$I_{OH} = -12$ mA	2.6		V
$V_{OL}$	Output Low Voltage	Q[4:1]	$I_{OL} = 12$ mA		0.5	V

**LVC MOS DC CHARACTERISTICS,  $V_{DD} = 2.5$  V  $\pm$  5%,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

$V_{IH}$	Input High Voltage		$0.65 * V_{DD}$		3.6	V
$V_{IL}$	Input Low Voltage		-0.3		$0.35 * V_{DD}$	V
$I_{IH}$	Input High Current	CLK_IN	$V_{DD} = V_{IN} = 2.625$ V		165	$\mu\text{A}$
		OE	$V_{DD} = V_{IN} = 2.625$ V		5	$\mu\text{A}$
$I_{IL}$	Input Low Current	CLK_IN	$V_{DD} = 2.625$ V, $V_{IN} = 0$ V	-5		$\mu\text{A}$
		OE	$V_{DD} = 2.625$ V, $V_{IN} = 0$ V	-150		$\mu\text{A}$

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**Table 5. DC ELECTRICAL CHARACTERISTICS**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>LVC MOS DC CHARACTERISTICS, <math>V_{DD} = 2.5 \text{ V} \pm 5\%</math>, <math>T_A = -40^\circ\text{C}</math> to <math>85^\circ\text{C}</math></b>						
$V_{OH}$	Output High Voltage	Q[4:1]	$I_{OH} = -12 \text{ mA}$	1.8		V
$V_{OL}$	Output Low Voltage	Q[4:1]	$I_{OL} = 12 \text{ mA}$		0.5	V
<b>LVC MOS DC CHARACTERISTICS, <math>V_{DD} = 1.8 \text{ V} \pm 0.15 \text{ V}</math>, <math>T_A = -40^\circ\text{C}</math> to <math>85^\circ\text{C}</math></b>						
$V_{IH}$	Input High Voltage			$0.65 * V_{DD}$	3.6	V
$V_{IL}$	Input Low Voltage			-0.3	$0.35 * V_{DD}$	V
$I_{IH}$	Input High Current	CLK_IN	$V_{DD} = V_{IN} = 1.95 \text{ V}$		165	$\mu\text{A}$
		OE			5	$\mu\text{A}$
$I_{IL}$	Input Low Current	CLK_IN	$V_{DD} = 1.95 \text{ V}, V_{IN} = 0 \text{ V}$	-5		$\mu\text{A}$
		OE	$V_{DD} = 1.95 \text{ V}, V_{IN} = 0 \text{ V}$	-150		$\mu\text{A}$
$V_{OH}$	Output High Voltage	Q[4:1]	$I_{OH} = -6 \text{ mA}$	$V_{DD} - 0.45$		V
$V_{OL}$	Output Low Voltage	Q[4:1]	$I_{OL} = 6 \text{ mA}$		0.45	V
<b>LVC MOS DC CHARACTERISTICS, <math>V_{DD} = 1.5 \text{ V} \pm 0.1 \text{ V}</math>, <math>T_A = -40^\circ\text{C}</math> to <math>85^\circ\text{C}</math></b>						
$V_{IH}$	Input High Voltage			$0.65 * V_{DD}$	3.6	V
$V_{IL}$	Input Low Voltage			-0.3	$0.35 * V_{DD}$	V
$I_{IH}$	Input High Current	CLK_IN	$V_{DD} = V_{IN} = 1.6 \text{ V}$		165	$\mu\text{A}$
		OE	$V_{DD} = V_{IN} = 1.6 \text{ V}$		5	$\mu\text{A}$
$I_{IL}$	Input Low Current	CLK_IN	$V_{DD} = 1.6 \text{ V}, V_{IN} = 0 \text{ V}$	-5		$\mu\text{A}$
		OE	$V_{DD} = 1.6 \text{ V}, V_{IN} = 0 \text{ V}$	-150		$\mu\text{A}$
$V_{OH}$	Output High Voltage	Q[4:1]	$I_{OH} = -4 \text{ mA}$	$0.75 * V_{DD}$		V
$V_{OL}$	Output Low Voltage	Q[4:1]	$I_{OL} = 4 \text{ mA}$		$0.25 * V_{DD}$	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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**Table 6. AC ELECTRICAL CHARACTERISTICS**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**AC CHARACTERISTICS,  $V_{DD} = 3.3\text{ V} \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

$f_{OUT}$	Output Frequency				160	MHz
$t_{PLH}$	Propagation Delay (low to high transition); (Notes 4, 8)		0.7		2.1	ns
$t_{PHL}$	Propagation Delay (high to low transition); (Notes 4, 8)		0.7		2.1	ns
$t_{PLZ}, t_{PHZ}$	Disable Time, (active to high-impedance)				10	ns
$t_{PZL}, t_{PZH}$	Enable Time, (high-impedance to active)				10	ns
$tsk(o)$	Output Skew; (Notes 5, 6)				250	ps
$tsk(pp)$	Part-to-Part Skew; (Notes 5, 7)				800	ps
$t_{jit}$	Buffer Additive Phase Jitter, RMS	25 MHz, Integration Range: 12 kHz – 5 MHz		0.094		ps
$t_R / t_F$	Output Rise/Fall Time	10% to 90%	0.33		1.2	ns
odc	Output Duty Cycle		48		53	%

**AC CHARACTERISTICS,  $V_{DD} = 2.5\text{ V} \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

$f_{OUT}$	Output Frequency				160	MHz
$t_{PLH}$	Propagation Delay (low to high transition); (Notes 4, 8)		0.8		2.0	ns
$t_{PHL}$	Propagation Delay (high to low transition); (Notes 4, 8)		0.8		2.0	ns
$t_{PLZ}, t_{PHZ}$	Disable Time (active to high-impedance)				10	ns
$t_{PZL}, t_{PZH}$	Enable Time (high-impedance to active)				10	ns
$tsk(o)$	Output Skew; (Notes 5, 6)				250	ps
$tsk(pp)$	Part-to-Part Skew; (Notes 5, 7)				800	ps
$t_{jit}$	Buffer Additive Phase Jitter, RMS	25 MHz, Integration Range: 12 kHz – 5 MHz		0.076		ps
$t_R / t_F$	Output Rise/Fall Time	10% to 90%	0.33		1.2	ns
odc	Output Duty Cycle		45		53	%

**AC CHARACTERISTICS,  $V_{DD} = 1.8\text{ V} \pm 0.15\text{ V}$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

$f_{OUT}$	Output Frequency				160	MHz
$t_{PLH}$	Propagation Delay (low to high transition); (Notes 4, 8)		1.1		2.8	ns
$t_{PHL}$	Propagation Delay (high to low transition); (Notes 4, 8)		1.1		2.8	ns
$t_{PLZ}, t_{PHZ}$	Disable Time (active to high-impedance)				10	ns
$t_{PZL}, t_{PZH}$	Enable Time (high-impedance to active)				10	ns
$tsk(o)$	Output Skew; (Notes 5, 6)				250	ps
$tsk(pp)$	Part-to-Part Skew; (Notes 5, 7)				800	ps
$t_{jit}$	Buffer Additive Phase Jitter, RMS	25 MHz, Integration Range: 12 kHz – 5MHz		0.193		ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm.

3. Characterized up to  $F_{OUT} \leq 150\text{ MHz}$ .
4. Measured from the  $V_{DD}/2$  of the input to  $V_{DD}/2$  of the output.
5. This parameter is defined in accordance with JEDEC Standard 65.
6. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at  $V_{DD}/2$ .
7. Defined as skew between outputs on different devices operating at the same supply voltage, same temperature, same frequency and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at  $V_{DD}/2$ .
8. With rail to rail input clock.

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**Table 6. AC ELECTRICAL CHARACTERISTICS**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>AC CHARACTERISTICS, <math>V_{DD} = 1.8\text{ V} \pm 0.15\text{ V}</math>, <math>T_A = -40^\circ\text{C}</math> to <math>85^\circ\text{C}</math></b>						
$t_R / t_F$	Output Rise/Fall Time	0.63 V to 1.17 V	0.11		0.6	ns
odc	Output Duty Cycle		47		53	%
<b>AC CHARACTERISTICS, <math>V_{DD} = 1.5\text{ V} \pm 0.1\text{ V}</math>, <math>T_A = -40^\circ\text{C}</math> to <math>85^\circ\text{C}</math></b>						
$f_{OUT}$	Output Frequency				160	MHz
$t_{PLH}$	Propagation Delay (low to high transition); (Notes 4, 8)		1.5		3.5	ns
$t_{PHL}$	Propagation Delay (high to low transition); (Notes 4, 8)		1.5		3.5	ns
$t_{PLZ}$ , $t_{PHZ}$	Disable Time (active to high-impedance)				10	ns
$t_{PZL}$ , $t_{PZH}$	Enable Time (high-impedance to active)				10	ns
tsk(o)	Output Skew; (Notes 5, 6)				250	ps
tsk(pp)	Part-to-Part Skew; (Notes 5, 7)				800	ps
tjit	Buffer Additive Phase Jitter, RMS	25 MHz, Integration Range: 12 kHz – 5 MHz		0.266		ps
$t_R / t_F$	Output Rise/Fall Time	0.525 V to 0.975 V	0.11		0.6	ns
odc	Output Duty Cycle		47		53	%

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

3. Characterized up to  $F_{OUT} \leq 150\text{ MHz}$ .
4. Measured from the  $V_{DD}/2$  of the input to  $V_{DD}/2$  of the output.
5. This parameter is defined in accordance with JEDEC Standard 65.
6. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at  $V_{DD}/2$ .
7. Defined as skew between outputs on different devices operating at the same supply voltage, same temperature, same frequency and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at  $V_{DD}/2$ .
8. With rail to rail input clock.

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## Parameter Measurement Information

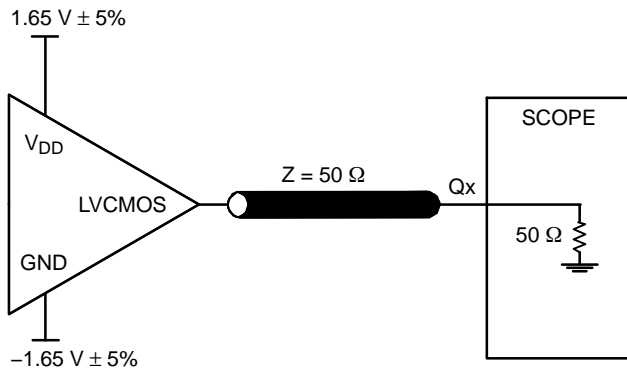


Figure 3. 3.3 V Output Load AC Test Circuit

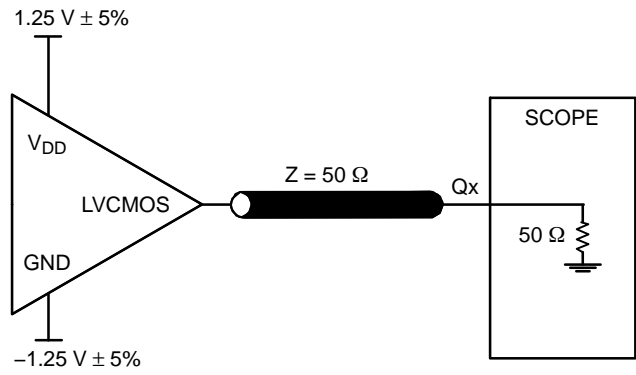


Figure 4. 2.5 V Output Load AC Test Circuit

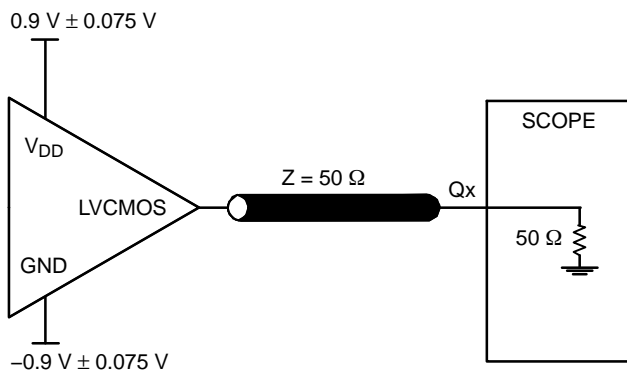


Figure 5. 1.8 V Output Load AC Test Circuit

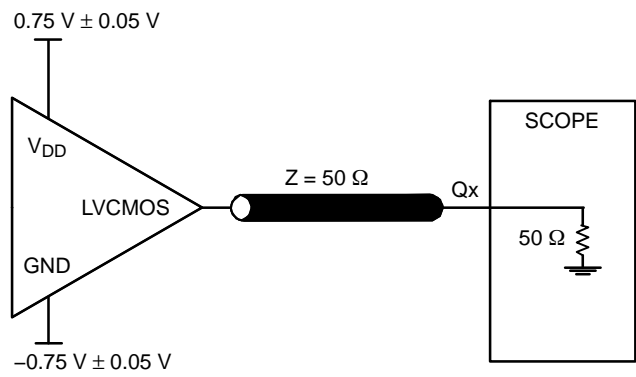


Figure 6. 1.5 V Output Load AC Test Circuit

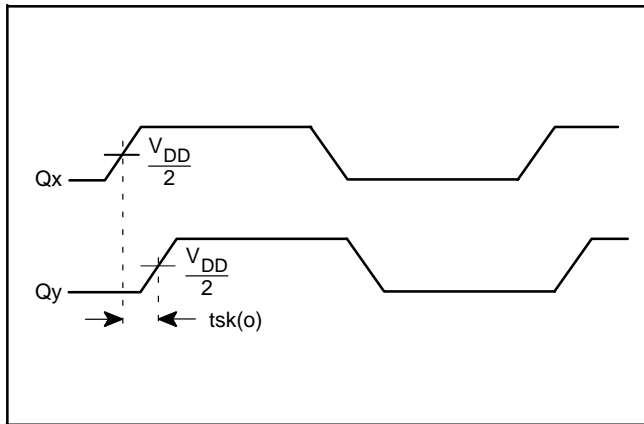


Figure 7. Output Skew

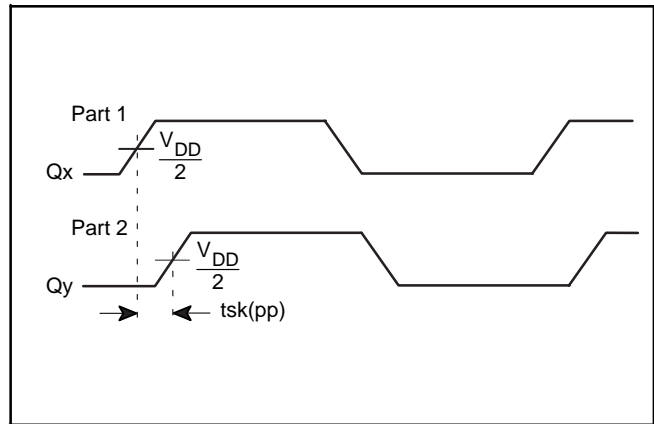


Figure 8. Part-to-Part Skew

Parameter Measurement Information, (continued)

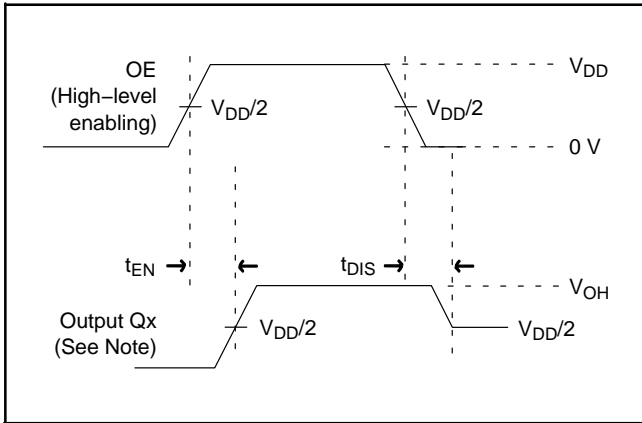


Figure 9. Output Enable/Disable Time

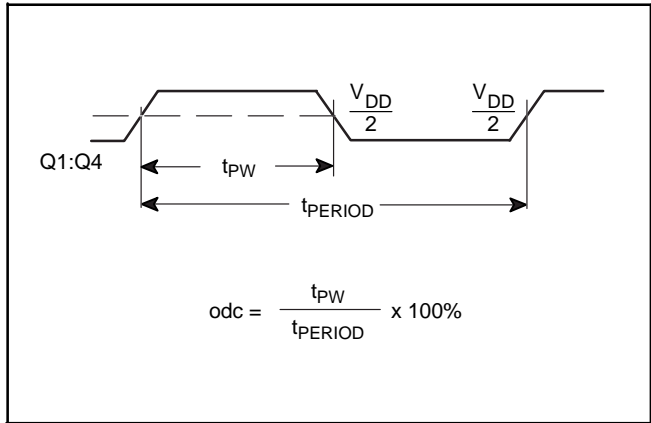


Figure 10. Output Duty Cycle/Pulse Width/Period

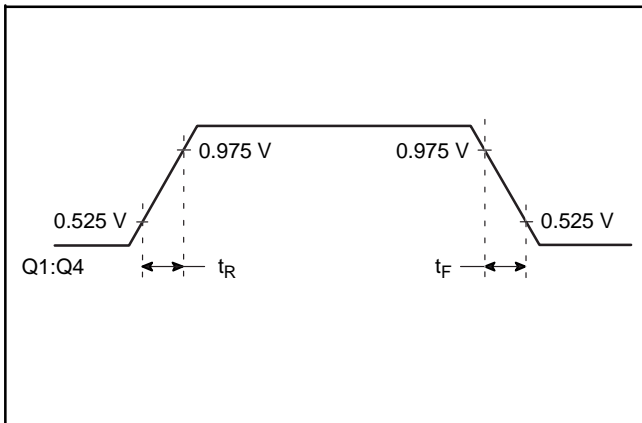


Figure 11. 1.5 V Output Rise/Fall Time

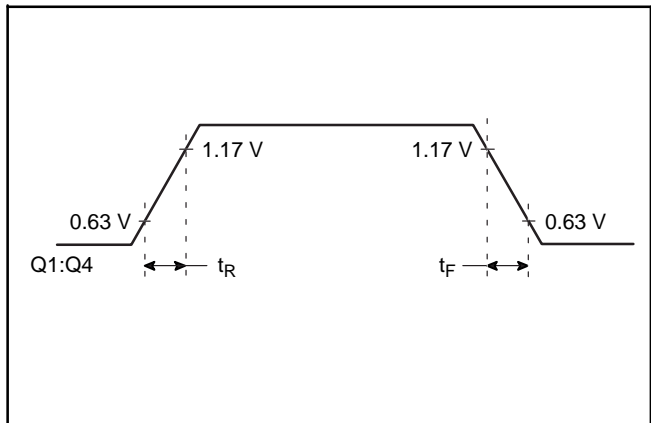


Figure 12. 1.8 V Output Rise/Fall Time

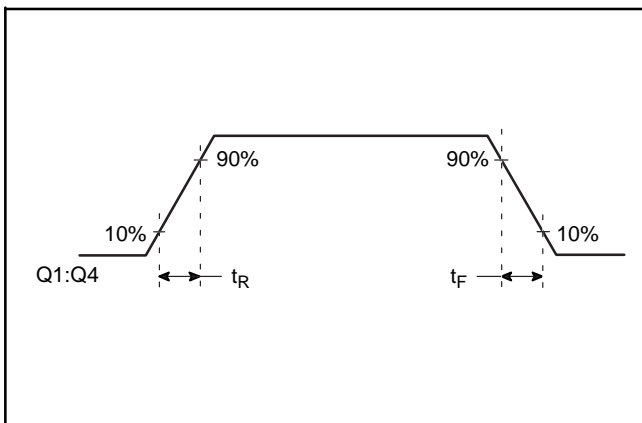


Figure 13. 2.5 V and 3.3 V Output Rise/Fall Time

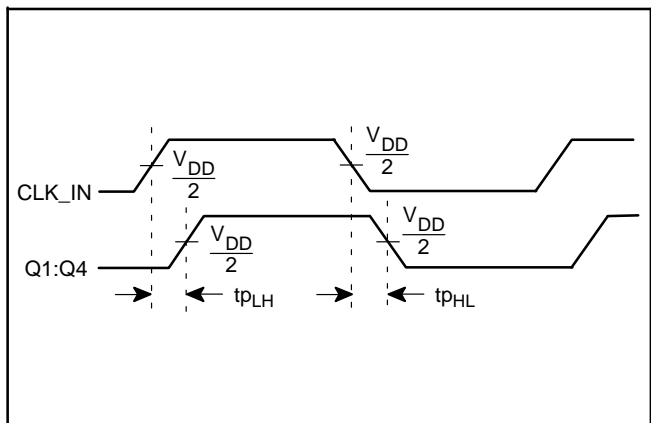


Figure 14. Propagation Delay



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**Table 7. THERMAL RESISTANCE  $\theta_{JA}$**

$\theta_{JA}$ by Velocity			
<b>FOR 8 LEAD SOIC, FORCED CONVECTION</b>			
Meters per Second	<b>0</b>	<b>1</b>	<b>2.5</b>
Multi-Layer PCB, JEDEC Standard Test Boards	102.5°C/W	93.5°C/W	88.6°C/W
<b>FOR 8 LEAD TSSOP, FORCED CONVECTION</b>			
Meters per Second	<b>0</b>	<b>1</b>	<b>2.5</b>
Multi-Layer PCB, JEDEC Standard Test Boards	151.2°C/W	145.9°C/W	143.3°C/W
$\theta_{JA}$ by Velocity			

**Table 8. ORDERING INFORMATION**

Device	Package	Shipping†
NB3U1548CDG	SOIC-8 (Pb-Free)	96 Units / Tube
NB3U1548CDR2G	SOIC-8 (Pb-Free)	3000 / Tape & Reel
NB3U1548CDTR2G	TSSOP-8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

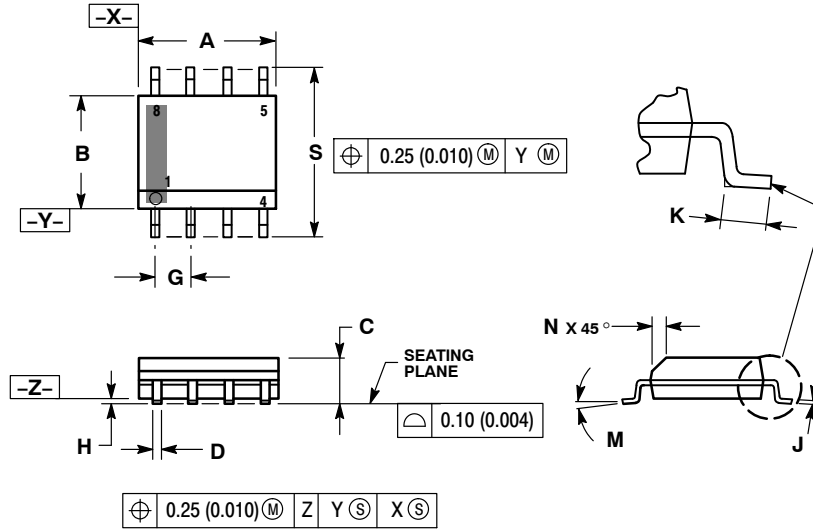
ON Semiconductor®



SCALE 1:1

SOIC-8 NB  
CASE 751-07  
ISSUE AK

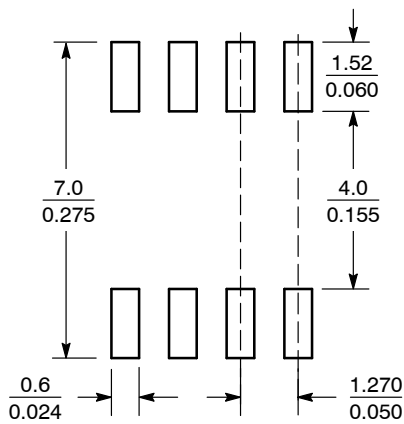
DATE 16 FEB 2011



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
  6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

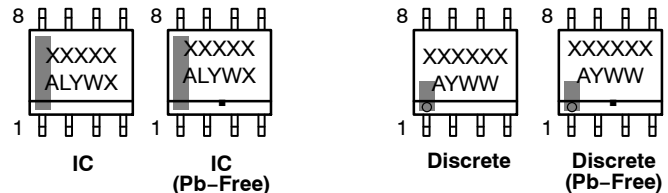
### SOLDERING FOOTPRINT\*



SCALE 6:1 (mm/inches)

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### GENERIC MARKING DIAGRAM\*



XXXXX = Specific Device Code  
 A = Assembly Location  
 L = Wafer Lot  
 Y = Year  
 W = Work Week  
 ■ = Pb-Free Package

XXXXXX = Specific Device Code  
 A = Assembly Location  
 Y = Year  
 WW = Work Week  
 ■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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DESCRIPTION:	SOIC-8 NB	PAGE 1 OF 2

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**SOIC-8 NB**  
**CASE 751-07**  
**ISSUE AK**

DATE 16 FEB 2011

- |  |   |   |   |
|--|---|---|---|
| <p><b>STYLE 1:</b><br/> PIN 1. EMITTER<br/> 2. COLLECTOR<br/> 3. COLLECTOR<br/> 4. EMITTER<br/> 5. EMITTER<br/> 6. BASE<br/> 7. BASE<br/> 8. EMITTER</p>   | <p><b>STYLE 2:</b><br/> PIN 1. COLLECTOR, DIE, #1<br/> 2. COLLECTOR, #1<br/> 3. COLLECTOR, #2<br/> 4. COLLECTOR, #2<br/> 5. BASE, #2<br/> 6. EMITTER, #2<br/> 7. BASE, #1<br/> 8. EMITTER, #1</p>               | <p><b>STYLE 3:</b><br/> PIN 1. DRAIN, DIE #1<br/> 2. DRAIN, #1<br/> 3. DRAIN, #2<br/> 4. DRAIN, #2<br/> 5. GATE, #2<br/> 6. SOURCE, #2<br/> 7. GATE, #1<br/> 8. SOURCE, #1</p>                            | <p><b>STYLE 4:</b><br/> PIN 1. ANODE<br/> 2. ANODE<br/> 3. ANODE<br/> 4. ANODE<br/> 5. ANODE<br/> 6. ANODE<br/> 7. ANODE<br/> 8. COMMON CATHODE</p>   |
| <p><b>STYLE 5:</b><br/> PIN 1. DRAIN<br/> 2. DRAIN<br/> 3. DRAIN<br/> 4. DRAIN<br/> 5. GATE<br/> 6. GATE<br/> 7. SOURCE<br/> 8. SOURCE</p>   | <p><b>STYLE 6:</b><br/> PIN 1. SOURCE<br/> 2. DRAIN<br/> 3. DRAIN<br/> 4. SOURCE<br/> 5. SOURCE<br/> 6. GATE<br/> 7. GATE<br/> 8. SOURCE</p>  | <p><b>STYLE 7:</b><br/> PIN 1. INPUT<br/> 2. EXTERNAL BYPASS<br/> 3. THIRD STAGE SOURCE<br/> 4. GROUND<br/> 5. DRAIN<br/> 6. GATE 3<br/> 7. SECOND STAGE Vd<br/> 8. FIRST STAGE Vd</p>                    | <p><b>STYLE 8:</b><br/> PIN 1. COLLECTOR, DIE #1<br/> 2. BASE, #1<br/> 3. BASE, #2<br/> 4. COLLECTOR, #2<br/> 5. COLLECTOR, #2<br/> 6. EMITTER, #2<br/> 7. EMITTER, #1<br/> 8. COLLECTOR, #1</p>                              |
| <p><b>STYLE 9:</b><br/> PIN 1. EMITTER, COMMON<br/> 2. COLLECTOR, DIE #1<br/> 3. COLLECTOR, DIE #2<br/> 4. EMITTER, COMMON<br/> 5. EMITTER, COMMON<br/> 6. BASE, DIE #2<br/> 7. BASE, DIE #1<br/> 8. EMITTER, COMMON</p> | <p><b>STYLE 10:</b><br/> PIN 1. GROUND<br/> 2. BIAS 1<br/> 3. OUTPUT<br/> 4. GROUND<br/> 5. GROUND<br/> 6. BIAS 2<br/> 7. INPUT<br/> 8. GROUND</p>  | <p><b>STYLE 11:</b><br/> PIN 1. SOURCE 1<br/> 2. GATE 1<br/> 3. SOURCE 2<br/> 4. GATE 2<br/> 5. DRAIN 2<br/> 6. DRAIN 2<br/> 7. DRAIN 1<br/> 8. DRAIN 1</p>   | <p><b>STYLE 12:</b><br/> PIN 1. SOURCE<br/> 2. SOURCE<br/> 3. SOURCE<br/> 4. GATE<br/> 5. DRAIN<br/> 6. DRAIN<br/> 7. DRAIN<br/> 8. DRAIN</p>   |
| <p><b>STYLE 13:</b><br/> PIN 1. N.C.<br/> 2. SOURCE<br/> 3. SOURCE<br/> 4. GATE<br/> 5. DRAIN<br/> 6. DRAIN<br/> 7. DRAIN<br/> 8. DRAIN</p>  | <p><b>STYLE 14:</b><br/> PIN 1. N-SOURCE<br/> 2. N-GATE<br/> 3. P-SOURCE<br/> 4. P-GATE<br/> 5. P-DRAIN<br/> 6. P-DRAIN<br/> 7. N-DRAIN<br/> 8. N-DRAIN</p>   | <p><b>STYLE 15:</b><br/> PIN 1. ANODE 1<br/> 2. ANODE 1<br/> 3. ANODE 1<br/> 4. ANODE 1<br/> 5. CATHODE, COMMON<br/> 6. CATHODE, COMMON<br/> 7. CATHODE, COMMON<br/> 8. CATHODE, COMMON</p>               | <p><b>STYLE 16:</b><br/> PIN 1. EMITTER, DIE #1<br/> 2. BASE, DIE #1<br/> 3. EMITTER, DIE #2<br/> 4. BASE, DIE #2<br/> 5. COLLECTOR, DIE #2<br/> 6. COLLECTOR, DIE #2<br/> 7. COLLECTOR, DIE #1<br/> 8. COLLECTOR, DIE #1</p> |
| <p><b>STYLE 17:</b><br/> PIN 1. VCC<br/> 2. V2OUT<br/> 3. V1OUT<br/> 4. TXE<br/> 5. RXE<br/> 6. VEE<br/> 7. GND<br/> 8. ACC</p>  | <p><b>STYLE 18:</b><br/> PIN 1. ANODE<br/> 2. ANODE<br/> 3. SOURCE<br/> 4. GATE<br/> 5. DRAIN<br/> 6. DRAIN<br/> 7. CATHODE<br/> 8. CATHODE</p>   | <p><b>STYLE 19:</b><br/> PIN 1. SOURCE 1<br/> 2. GATE 1<br/> 3. SOURCE 2<br/> 4. GATE 2<br/> 5. DRAIN 2<br/> 6. MIRROR 2<br/> 7. DRAIN 1<br/> 8. MIRROR 1</p>   | <p><b>STYLE 20:</b><br/> PIN 1. SOURCE (N)<br/> 2. GATE (N)<br/> 3. SOURCE (P)<br/> 4. GATE (P)<br/> 5. DRAIN<br/> 6. DRAIN<br/> 7. DRAIN<br/> 8. DRAIN</p>   |
| <p><b>STYLE 21:</b><br/> PIN 1. CATHODE 1<br/> 2. CATHODE 2<br/> 3. CATHODE 3<br/> 4. CATHODE 4<br/> 5. CATHODE 5<br/> 6. COMMON ANODE<br/> 7. COMMON ANODE<br/> 8. CATHODE 6</p>  | <p><b>STYLE 22:</b><br/> PIN 1. I/O LINE 1<br/> 2. COMMON CATHODE/VCC<br/> 3. COMMON CATHODE/VCC<br/> 4. I/O LINE 3<br/> 5. COMMON ANODE/GND<br/> 6. I/O LINE 4<br/> 7. I/O LINE 5<br/> 8. COMMON ANODE/GND</p> | <p><b>STYLE 23:</b><br/> PIN 1. LINE 1 IN<br/> 2. COMMON ANODE/GND<br/> 3. COMMON ANODE/GND<br/> 4. LINE 2 IN<br/> 5. LINE 2 OUT<br/> 6. COMMON ANODE/GND<br/> 7. COMMON ANODE/GND<br/> 8. LINE 1 OUT</p> | <p><b>STYLE 24:</b><br/> PIN 1. BASE<br/> 2. EMITTER<br/> 3. COLLECTOR/ANODE<br/> 4. COLLECTOR/ANODE<br/> 5. CATHODE<br/> 6. CATHODE<br/> 7. COLLECTOR/ANODE<br/> 8. COLLECTOR/ANODE</p>                                      |
| <p><b>STYLE 25:</b><br/> PIN 1. VIN<br/> 2. N/C<br/> 3. REXT<br/> 4. GND<br/> 5. IOUT<br/> 6. IOUT<br/> 7. IOUT<br/> 8. IOUT</p>   | <p><b>STYLE 26:</b><br/> PIN 1. GND<br/> 2. dv/dt<br/> 3. ENABLE<br/> 4. ILIMIT<br/> 5. SOURCE<br/> 6. SOURCE<br/> 7. SOURCE<br/> 8. VCC</p>  | <p><b>STYLE 27:</b><br/> PIN 1. ILIMIT<br/> 2. OVLO<br/> 3. UVLO<br/> 4. INPUT+<br/> 5. SOURCE<br/> 6. SOURCE<br/> 7. SOURCE<br/> 8. DRAIN</p>  | <p><b>STYLE 28:</b><br/> PIN 1. SW_TO_GND<br/> 2. DASIC OFF<br/> 3. DASIC_SW_DET<br/> 4. GND<br/> 5. V_MON<br/> 6. VBULK<br/> 7. VBULK<br/> 8. VIN</p>  |
| <p><b>STYLE 29:</b><br/> PIN 1. BASE, DIE #1<br/> 2. EMITTER, #1<br/> 3. BASE, #2<br/> 4. EMITTER, #2<br/> 5. COLLECTOR, #2<br/> 6. COLLECTOR, #2<br/> 7. COLLECTOR, #1<br/> 8. COLLECTOR, #1</p>                        | <p><b>STYLE 30:</b><br/> PIN 1. DRAIN 1<br/> 2. DRAIN 1<br/> 3. GATE 2<br/> 4. SOURCE 2<br/> 5. SOURCE 1/DRAIN 2<br/> 6. SOURCE 1/DRAIN 2<br/> 7. SOURCE 1/DRAIN 2<br/> 8. GATE 1</p>                           |   |   |

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

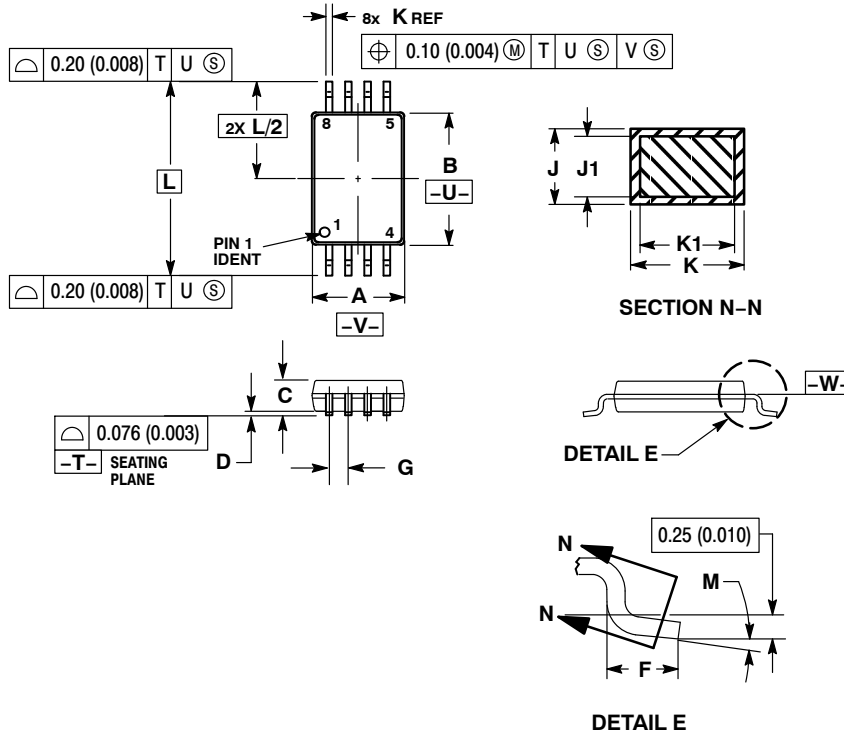
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SCALE 2:1

TSSOP-8  
CASE 948S-01  
ISSUE C

DATE 20 JUN 2008

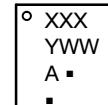


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	4.30	4.50	0.169	0.177
C	---	1.10	---	0.043
D	0.05	0.15	0.002	0.006
F	0.50	0.70	0.020	0.028
G	0.65 BSC		0.026 BSC	
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

GENERIC  
MARKING DIAGRAM\*



- XXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

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